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STATEMENT BY APPLICANT**

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JUN 25 2002

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Complete if Known

Application Number	09/944985
Filing Date	August 30, 2001
First Named Inventor	Bhattacharyya, Arup
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 1

Attorney Docket No: 01303.023US1

US PATENT DOCUMENTS

Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
TT	US-4870470	09/26/1989	Bass Jr. et al	357	23.5	10/16/1987

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TT	J	BHATTACHARYYA, A., "Physical & Electrical Characteristics of LPCVD Silicon Rich Nitride", <u>ECS Technical Digest</u> , J. Eletrochem. Soc., 131(11), 691 RDP, New Orleans,(1984), 469C	
TT	J	BLAUWE, J., et al. , "A novel, aerosol-nanocrystal floating-gate device for non-volatile memory applications", <u>IEDM</u> , (2000), pp. 683-686	
TT		HAN, K., et al. , "Characteristics of P-Channel Si Nano-Crystal Memory", <u>IEDM</u> , (2000),pp. 309-312	
TT		LEE, J., "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al ₂ O ₃ Gate Dielectric", <u>IEDM</u> , (2000),pp. 645-648	
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TT	J	MANCHANDA, L., "High K Dielectrics for CMOS and Flash", <u>Extended Abstracts</u> of the 1999 International Conference on Solid State Devices and Materials, Tokyo,(1999),pp. 150-151	
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